

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Marshall et al.

Docket No.: TI-31157

Serial No: TBD

Examiner: TBD

Filed: 12/13/01

Art Unit: TBD

For: MEMORY CELL WITH TRANSISTORS HAVING RELATIVELY HIGH
THRESHOLD VOLTAGES IN RESPONSE TO SELECTIVE GATE
DOPING

PRELIMINARY AMENDMENT

December 13, 2001

Assistant Commissioner for Patents

Washington, DC 20231

Dear Sir:

Please amend the above referenced application as follows:

In the Specification:

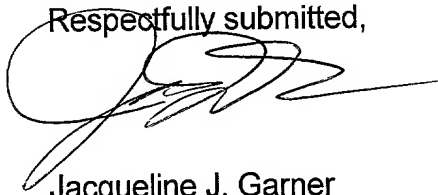
Page 1, before line 1, insert –This application claims priority under 35 USC §
119(e)(1) of provisional application number **60/259,324** filed **01/03/01**.

REMARKS

Entry of the foregoing amendment prior to examination is respectfully requested.

If the Examiner has any questions or other correspondence regarding this application, Applicant requests that the Examiner contact Applicant's attorney at the below listed telephone number and address.

Respectfully submitted,



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